BCR8CS

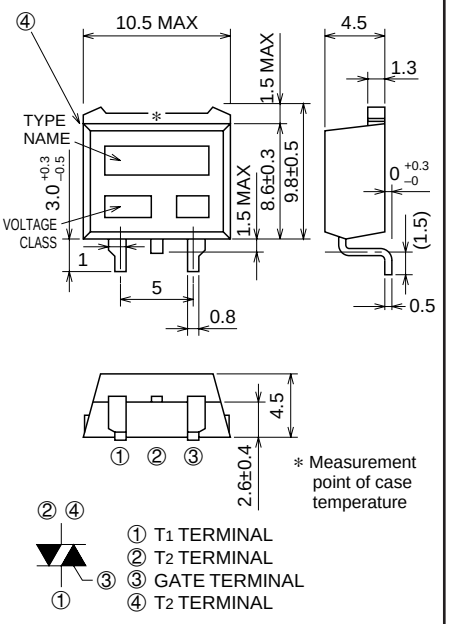
MEDIUM POWER USE

NON-INSULATED TYPE, PLANAR PASSIVATION TYPE

BCR8CS

- **$I_{T\ (RMS)}$ 8A**
- **V_{DRM} 400V/600V**
- **$I_{FGT\ I}$, $I_{RGT\ I}$, $I_{RGT\ III}$ 30mA (20mA) *5**

OUTLINE DRAWING Dimensions in mm



APPLICATION

Solid state relay, hybrid IC

MAXIMUM RATINGS

Symbol	Parameter	Voltage class		Unit
		8	12	
V_{DRM}	Repetitive peak off-state voltage *1	400	600	V
V_{DSM}	Non-repetitive peak off-state voltage *1	500	720	V

Symbol	Parameter	Conditions	Ratings	Unit
$I_{T\ (RMS)}$	RMS on-state current	Commercial frequency, sine full wave 360° conduction, T_C=105°C	8	A
I_{TSM}	Surge on-state current	60Hz sinewave 1 full cycle, peak value, non-repetitive	80	A
I^2t	I^2t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	26	A^2s
P_{GM}	Peak gate power dissipation		5	W
$P_{G\ (AV)}$	Average gate power dissipation		0.5	W
V_{GM}	Peak gate voltage		10	V
I_{GM}	Peak gate current		2	A
T_j	Junction temperature		–40 ~ +125	°C
T_{stg}	Storage temperature		–40 ~ +125	°C
—	Weight	Typical value	1.2	g

∗1. Gate open.

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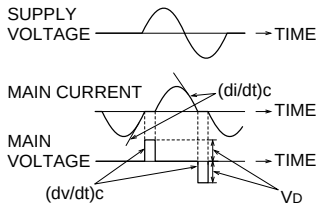
ELECTRICAL CHARACTERISTICS

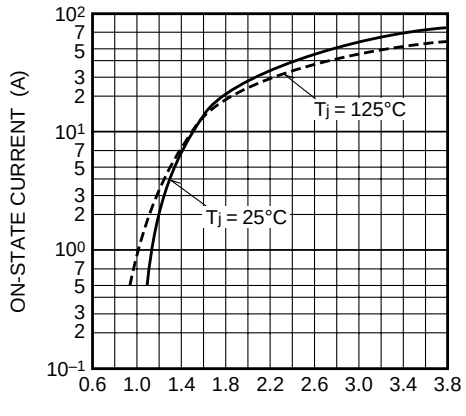
Symbol	Parameter		Test conditions	Limits			Unit
				Min.	Typ.	Max.	
I_{DRM}	Repetitive peak off-state current		T_j=125°C, V_{DRM} applied	—	—	2.0	mA
V_{TM}	On-state voltage		T_C=25°C, I_{TM}=12A, Instantaneous measurement	—	—	1.5	V
$V_{FGT\ I}$	Gate trigger voltage *2	Ⅰ	T_j=25°C, V_D=6V, R_L=6Ω, R_G=330Ω	—	—	1.5	V
$V_{RGT\ I}$		Ⅱ		—	—	1.5	V
$V_{RGT\ III}$		Ⅲ		—	—	1.5	V
$I_{FGT\ I}$	Gate trigger current *2	Ⅰ	T_j=25°C, V_D=6V, R_L=6Ω, R_G=330Ω	—	—	30*5	mA
$I_{RGT\ I}$		Ⅱ		—	—	30*5	mA
$I_{RGT\ III}$		Ⅲ		—	—	30*5	mA
V_{GD}	Gate non-trigger voltage		T_j=125°C, V_D=1/2V_{DRM}	0.2	—	—	V
$R_{th\ (j-c)}$	Thermal resistance		Junction to case *4	—	—	2.0	°C/W
$(dv/dt)_c$	Critical-rate of rise of off-state commutating voltage			*3	—	—	V/µs

*2. Measurement using the gate trigger characteristics measurement circuit.
*3. The critical-rate of rise of the off-state commutating voltage is shown in the table below.
*4. The contact thermal resistance $R_{th\ (c-f)}$ is 1.0°C/W.
*5. High sensitivity (I_{GT}≤20mA) is also available. (I_{GT} item ①)

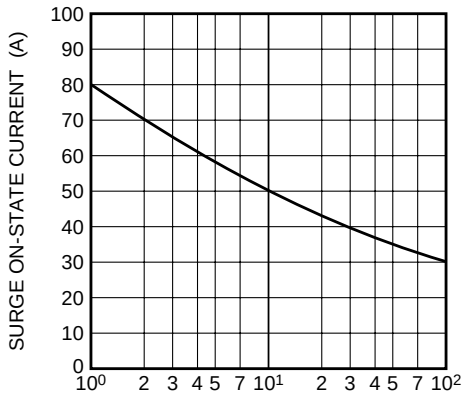
Voltage class	V_{DRM} (V)	$(dv/dt)_c$			Test conditions	Commutating voltage and current waveforms (inductive load)
		Symbol	Min.	Unit		
8	400	R	—	V/µs	1. Junction temperature T_j=125°C 2. Rate of decay of on-state commutating current $(di/dt)_c$=–4A/ms 3. Peak off-state voltage V_D=400V	
		L	10			
12	600	R	—			
		L	10			

PERFORMANCE CURVES

MAXIMUM ON-STATE CHARACTERISTICS



RATED SURGE ON-STATE CURRENT



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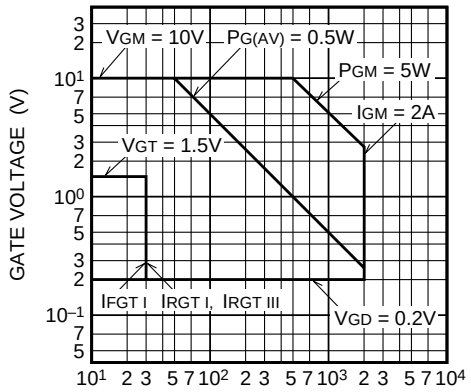
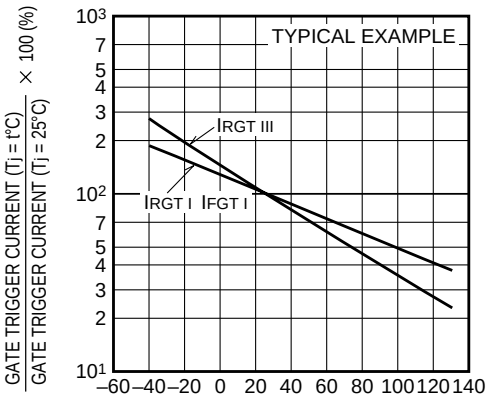
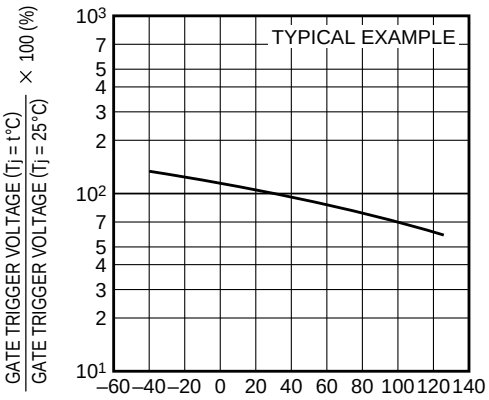
GATE CHARACTERISTICS



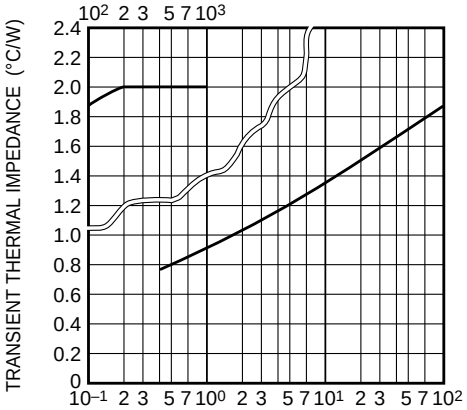
GATE TRIGGER CURRENT VS. JUNCTION TEMPERATURE



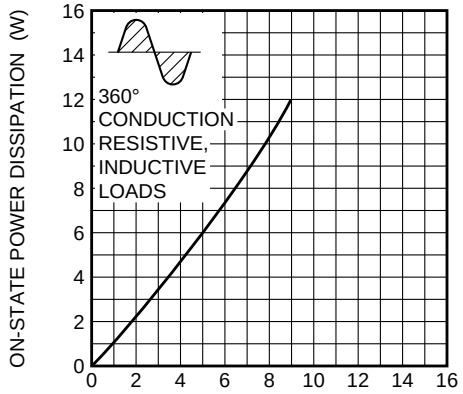
GATE TRIGGER VOLTAGE VS. JUNCTION TEMPERATURE



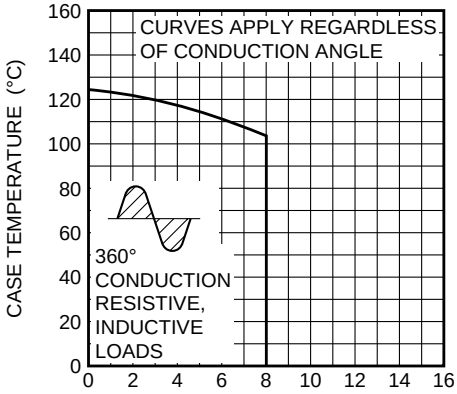
MAXIMUM TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO CASE)



MAXIMUM ON-STATE POWER DISSIPATION



ALLOWABLE CASE TEMPERATURE VS. RMS ON-STATE CURRENT



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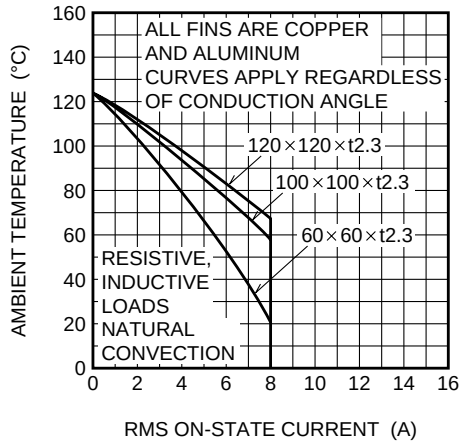
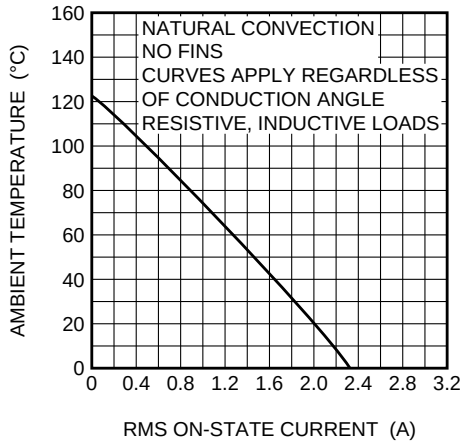
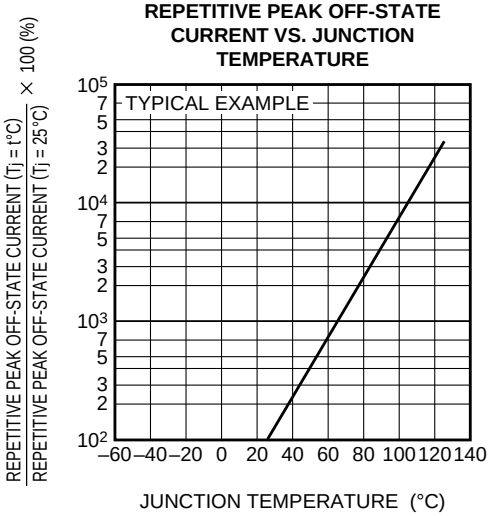
ALLOWABLE AMBIENT TEMPERATURE VS. RMS ON-STATE CURRENT



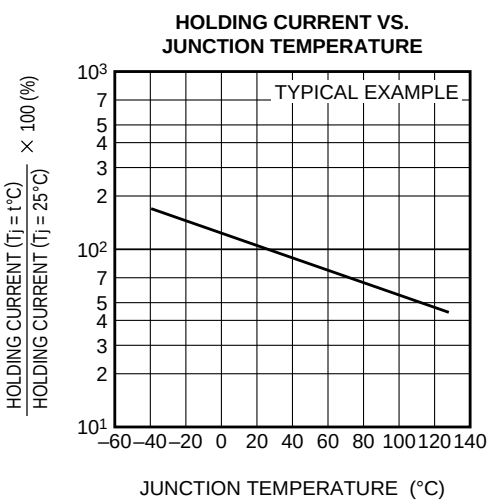
ALLOWABLE AMBIENT TEMPERATURE VS. RMS ON-STATE CURRENT



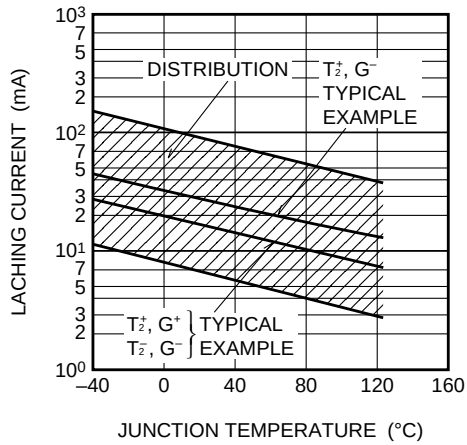
REPETITIVE PEAK OFF-STATE CURRENT VS. JUNCTION TEMPERATURE



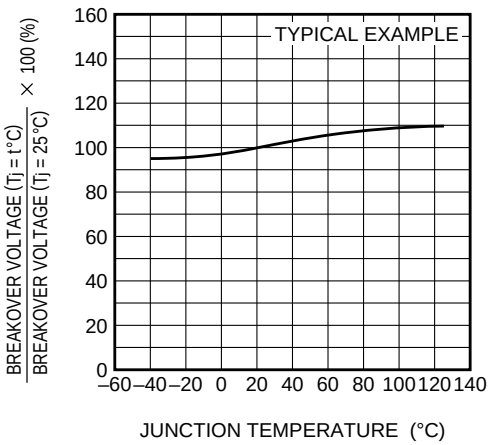
HOLDING CURRENT VS. JUNCTION TEMPERATURE



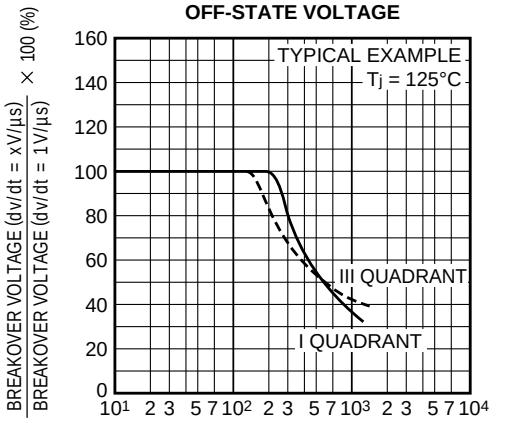
LACHING CURRENT VS. JUNCTION TEMPERATURE



BREAKOVER VOLTAGE VS. JUNCTION TEMPERATURE

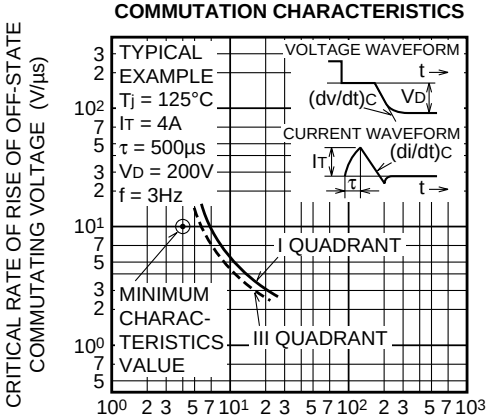


BREAKOVER VOLTAGE VS. RATE OF RISE OF OFF-STATE VOLTAGE



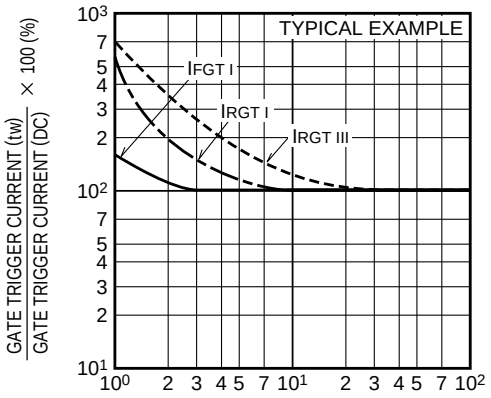
RATE OF RISE OF OFF-STATE VOLTAGE (V/µs)

COMMUTATION CHARACTERISTICS



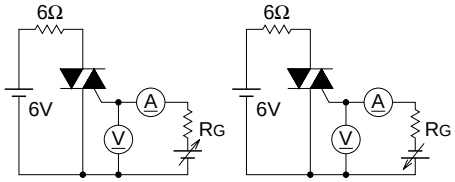
RATE OF DECAY OF ON-STATE COMMUTATING CURRENT (A/ms)

GATE TRIGGER CURRENT VS. GATE CURRENT PULSE WIDTH

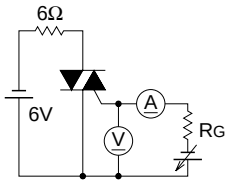


GATE CURRENT PULSE WIDTH (µs)

GATE TRIGGER CHARACTERISTICS TEST CIRCUITS



TEST PROCEDURE Ⅰ TEST PROCEDURE Ⅱ



TEST PROCEDURE Ⅲ